

DISPLACEMENT DAMAGE **TEST REPORT No. ATN-RR-333**

Issue/Rev: 1

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Date: 2015/05/28

R.L: 2015010918

Component No CS249/L2S Option 20 Gen. Spec.: MIL-PRF-19500 Det. Spec.: DWG CS249/L2S Amend.: N/A		Component Designation: CS249 Evaluation: X Acceptance Wafer: - Acceptance Lot: -	Irradiation Spec. No.: ESA/SCC 22900 Iss. 4 Project/Programme: CU1
Manuf.Name: ISOCOM LIMITED Address: GREAT BRITAIN		Test House: ATN Address: SEVILLA (SPAIN)	Facility Name: UCL Address: LOUVAIN LA NEUVE (BELGIUM)
Radiation Test Plan No.: ATN-RP 170 Iss.1		Sample Size: 5 Irradiation Devices: 4 Control Devices: 1	Date Code: 1508 Assembly Lot: 13053 Diffusion Run: 84609021073/3821D061111
Beam Energy: 60 MeV Flux: 1E8 [p/s cm ²]		Interest level: N/Av	Maximum Test Level: 8E11 p/cm ²
Irradiation Conditions: Biased: N/A Unbiased: 4 samples Test Circuit: Figure 1		Irradiation Measurements Interval: Remote test: X In situ Test:	Annealing Tests: N/A Biased: N/A Unbiased: N/A Test Circuit: N/A

Remark:

The results obtained during the irradiation test process show that the samples are sensitive to the cumulative fluence when are tested at a beam energy of 60 MeV up to an accumulated fluence of 8E11 p/cm². The IC/IF₁, IC/IF₂, IC/IF₃, IC/IF₄, IC/IF₅, IC/IF₆ and $V_{CE(SAT)}$ are the most affected parameters. Only the V_F, I_R, I_{CEO}, IC/IF₃ and IC/IF₅ remain within limits during the whole irradiation

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Date: 2015/05/28

Signature:

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Date: 2015/05/28

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